

# Discrete POWER & Signal



特力材料886-3-5753170 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787 Http://www. 100y. com. tw

### **NPN Switching Transistor**

This device is designed for high speed saturated switching applications at currents to 100 mA. Sourced from Process 21. See PN2369A for characteristics.

### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	15	-100 V
V <sub>CBO</sub>	Collector-Base Voltage	40	A CO
V <sub>EBO</sub>	Emitter-Base Voltage	4.5	W.Jook CO
I <sub>C</sub> Collector Current - Continuous		200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

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1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
W.	W. TIOOY.COM.TW	2N5769	N TIN	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C	
R <sub>eJC</sub>	Thermal Resistance, Junction to Case	125	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

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## **NPN Switching Transistor**

NPN Switching Transisto (continue  TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{C} = 10 \text{ mA}, I_{B} = 0$	15		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10 \mu\text{A}, I_{E} = 0$	40	TW	V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4.5	TW	V
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10  \mu \text{A},  I_{\rm B} = 0$	40	M.	V
Ісво	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, I_{E} = 0$ $V_{CB} = 20 \text{ V}, I_{E} = 0, T_{A} = 125 \text{ °C}$	M. C.	0.4 30	μA μA
I <sub>CES</sub>	Collector Cutoff Current	$V_{CE} = 20 \text{ V}, I_{B} = 0$	100	0.4	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.5 \text{ V}, I_{C} = 0$	1007.	1.0	μΑ
	M.TW WWW.100	$I_C = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $T_A = -55 ^{\circ}\text{C}$ $I_C = 30 \text{ mA}, V_{CE} = 0.40 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	20 30 20	ON.CO	M.T
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 30 \text{ mA}, V_{CE} = 0.40 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_A = 125 ^{\circ}\text{C}$ $I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	0.2 0.3 0.25	V
W.Joo	COM.	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.5	CV
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $T_A = 125 ^{\circ}\text{C}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.7 0.59	0.85 1.02	V
NWW.10	MY.COM.TW WY	$T_A = -55 ^{\circ}\text{C}$ $I_C = 30 \text{mA}, I_B = 3.0 \text{mA}$ $I_C = 100 \text{mA}, I_B = 10 \text{mA}$	0.59	1.02 1.15 1.6	V V V
SMALL S	IGNAL CHARACTERISTICS	WWW.100Y.COM.TW		MMM	100
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	N	4.0	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	5.0	WV	M.In.
SWITCHII	NG CHARACTERISTICS				
t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 10 mA,	$V_{-L,L}$	12	ns
	Turn-off Time	$I_{B1} = 3.0 \text{ mA}, I_{B2} = 1.5 \text{ mA}$	WILL	18	ns
off		$I_C = I_{B1} = I_{B2} = 10 \text{ mA}$			

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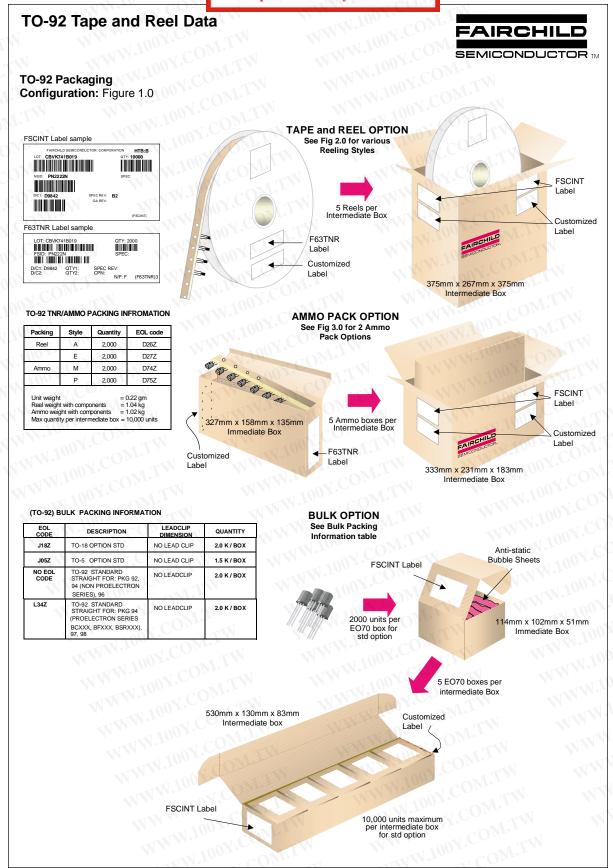
> WWW.100 WWW.10

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> > > WWW.100

<sup>\*</sup>Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0% WWW.100Y.C

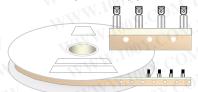
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### TO-92 Tape and Reel Data, continued

**TO-92 Reeling Style Configuration:** Figure 2.0

### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

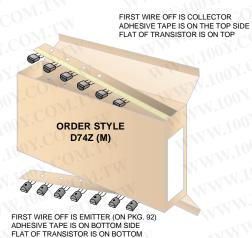
# Machine Option "E" (J)

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Style "E", D27Z, D71Z (s/h)

## TO-92 Radial Ammo Packaging Configuration: Figure 3.0





FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

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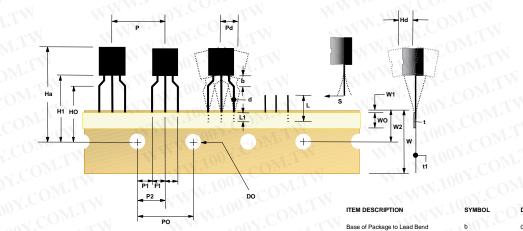
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# 100Y.COM.TW TO-92 Tape and Reel Data, continued

**User Direction of Feed** 

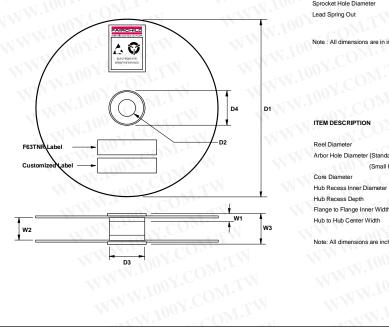
**TO-92 Tape and Reel Taping Dimension Configuration:** Figure 4.0 WWW.100Y.COM.TW 勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787

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TO-92 Reel Configuration: Figure 5.0



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TIEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Ha	0.928 (+/- 0.025)
Lead Clinch Height	НО	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment ( side/side )	Pd	0.040 (max)
Component Alignment ( front/back )	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0 .010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	1	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	wo	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

ITEM DESCRIPTION	SYSMBOL	MINIMUM	MAXIMUM	
Reel Diameter	D1	13.975	14.025	
Arbor Hole Diameter (Standard)	D2	1.160	1.200	
(Small Hole)	D2	0.650	0.700	
Core Diameter	D3	3.100	3.300	
Hub Recess Inner Diameter	D4	2.700	3.100	
Hub Recess Depth	W1	0.370	0.570	
Flange to Flange Inner Width	W2	1.630	1.690	
Hub to Hub Center Width	W3		2.090	

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### **TO-92 Package Dimensions** FAIRCHILD TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 2.0°TYP. TO-92 (92,94,96) 92 94 96 PIN В F В BF 0.76 0.36 В S 1 D Ε D 2 В S С G E D Ø0.060 [Ø1.52] 3 G С В S С G 0.010 [0.254] DEEP 0.48 0.30 勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-34970699 5.0°TYP. 胜特力电子(深圳) 86-755-83298787 Http://www. 100y. com. tw

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